2SA1585 TRANSISTOR (PNP)

1.BASE
2.COLLECTOR
3.EMITTER

SOT-23-3

FEATURES

- Low $V_{CE(sat)}$
- Excellent DC current gain characteristics. Power dissipation

MAXIMUM RATINGS* T_A=25℃ unless otherwise noted

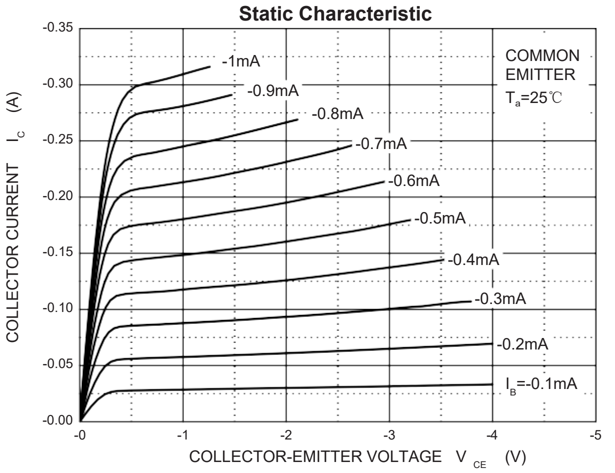
Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	-20	V
V_{CEO}	Collector-Emitter Voltage	-20	V
V_{EBO}	Emitter-Base Voltage	-6	V
I_C	Collector Current -Continuous	-2	A
P_C	Collector Power Dissipation	350	mW
T_J,T_{stg}	Operation Junction and Storage Temperature Range	-55-150	℃

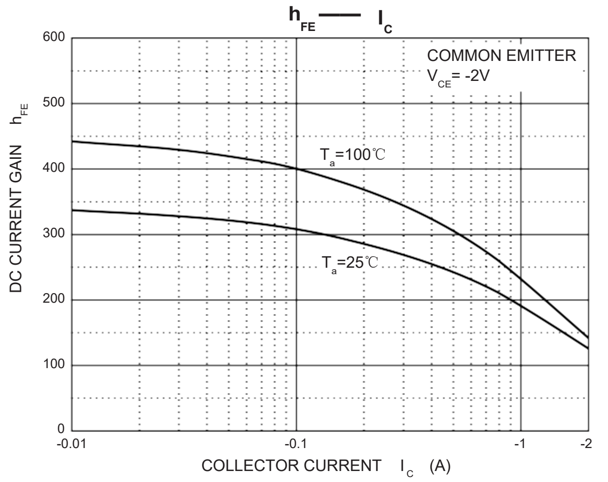
ELECTRICAL CHARACTERISTICS (Tamb=25℃ unless otherwise specified)

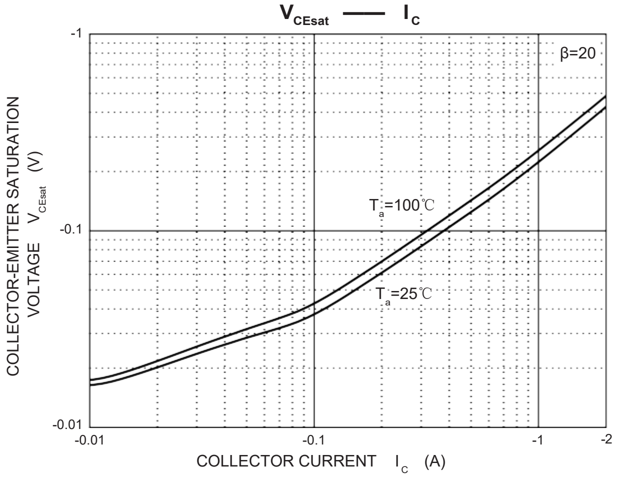
Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	I_C= -50⊠A , I_E=0	-20			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	I_C= -1 mA , I_B=0	-20			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E=- 50⊠A, I_C=0	-6			V
Collector cut-off current	I_{CBO}	V_{CB}=-20V , I_E=0			-0.1	⊠A
Emitter cut-off current	I_{EBO}	V_{EB}= -5V , I_C=0			-0.1	⊠A
DC current gain	h_{FE}	V_{CE}=-2 V, I_C= -0.1A	120		390	
Collector-emitter saturation voltage	V_{CEsat}	I_C= -2A, I_B=-0.1A			-0.5	V
Transition frequency	f_T	V_{CE}=-2V, I_C=-0.5A f=100MHz		240		MHz

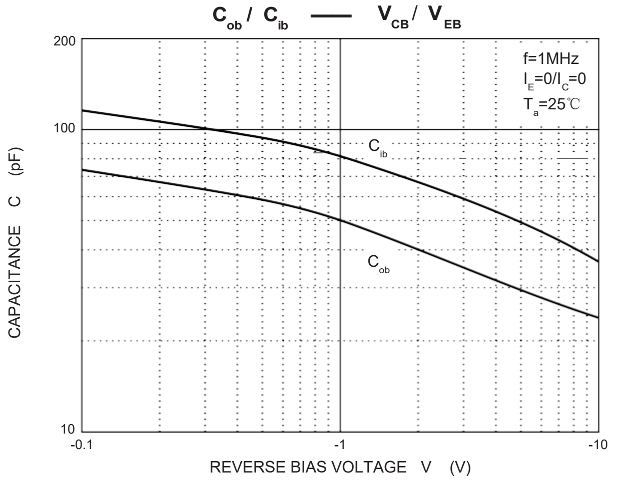
CLASSIFICATION OF h_{FE}

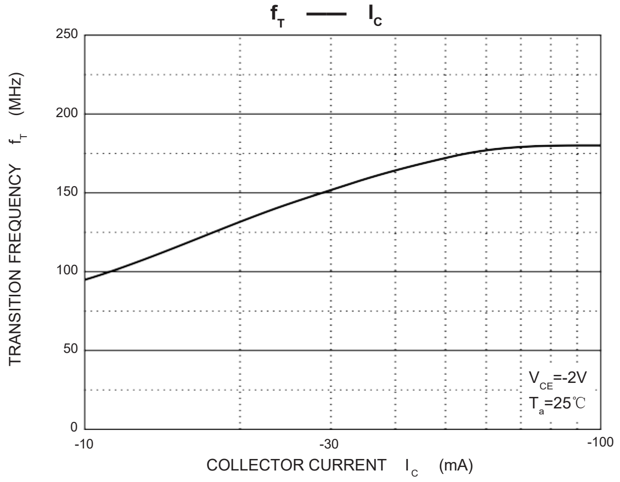
Rank	Q	R
Range	120-270	180-390
Marking	AEQ	AER

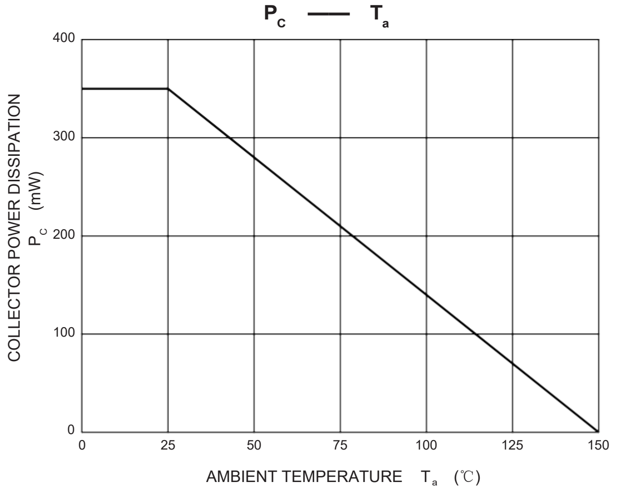

Static Characteristic


h_{FE} —— I_C


V_{CEsat} —— I_C


C_{ob} / C_{ib} —— V_{CB} / V_{EB}


f_T —— I_C


P_C —— T_a